

NCE2007N

SNCE N-Channel Enhancement Mode Power MOSFET

Description

The NCE2007N uses advanced trench technology to provide excellent R_{DS(ON)}, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

• $V_{DS} = 20V, I_D = 6.5A$

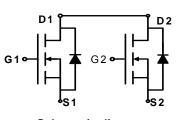
 $R_{DS(ON)}$ < 27m Ω @ V_{GS} =2.5V

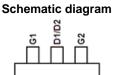
 $R_{DS(ON)}$ < 22m Ω @ V_{GS} =4.5V

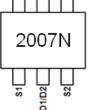
- High power and current handing capability
- Lead free product is acquired
- Surface mount package

Application

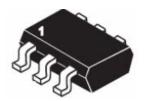
- Battery protection
- Load switch
- Power management







Marking and pin assignment



SOT23-6L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
2007N	NCE2007N	SOT23-6L	Ø330mm	12mm	3000 units

Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V _{DS}	20	V	
Gate-Source Voltage	V _{GS}	±12	V	
Drain Current-Continuous	I _D	6.5	А	
Drain Current-Pulsed (Note 1)	I _{DM}	25	А	
Maximum Power Dissipation	P _D	1.5	W	
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 150	°C	

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{ heta JA}$	83	°C/W
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Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						



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Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	20	-	ı	>
Zero Gate Voltage Drain Current	I _{DSS}	I_{DSS} V_{DS} =20V, V_{GS} =0V		-	1	μΑ
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±12V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250μA	0.5	0.7	1.2	V
Drain-Source On-State Resistance	В	V _{GS} =4.5V, I _D =6A	-	14.5	22	mΩ
Dialii-Source Oil-State Resistance	R _{DS(ON)}	V _{GS} =2.5V, I _D =5.5A	-	19	27	mΩ
Forward Transconductance	g FS	V _{DS} =5V,I _D =6A	-	10	ı	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{lss}	\/ -10\/\/ -0\/	-	900	-	PF
Output Capacitance	C _{oss}	V_{DS} =10V, V_{GS} =0V, F=1.0MHz	-	220	-	PF
Reverse Transfer Capacitance	C _{rss}	F = 1.0IVII 12	-	100	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	10	20	nS
Turn-on Rise Time	t _r	V _{DD} =10V,I _D =6A	-	11	25	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =4.5 V , R_{GEN} =6 Ω	-	35	70	nS
Turn-Off Fall Time	t _f		-	30	60	nS
Total Gate Charge	Qg	\/ =10\/ =6A	-	12	15	nC
Gate-Source Charge	Q _{gs}	V_{DS} =10V, I_{D} =6A, V_{GS} =4.5V	-	2.3	-	nC
Gate-Drain Charge	Q_{gd}	VGS-4.5V	-	1	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =6A	-	-	1.2	V
Diode Forward Current (Note 2)	I _S		-	-	6.5	Α

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- **3.** Pulse Test: Pulse Width ≤ 300μ s, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production



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Pb Free Product

Typical Electrical and Thermal Characteristics

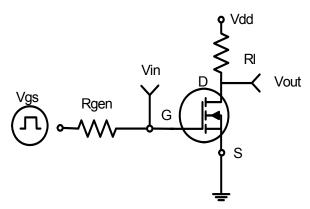


Figure 1:Switching Test Circuit

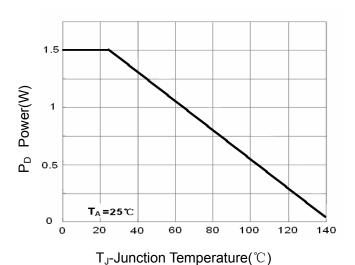


Figure 3 Power Dissipation

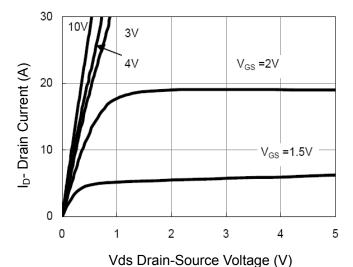


Figure 5 Output Characteristics

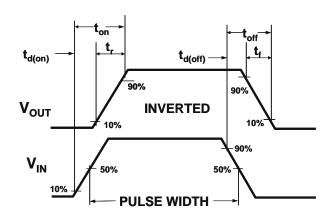


Figure 2:Switching Waveforms

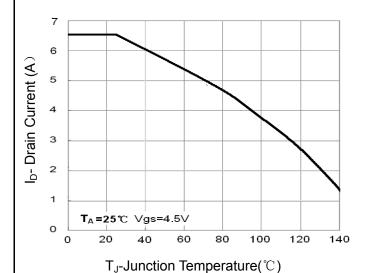


Figure 4 Drain Current

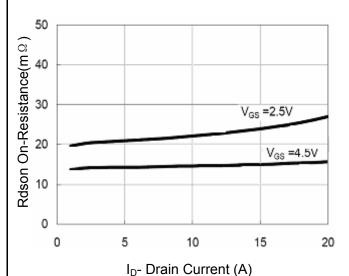


Figure 6 Drain-Source On-Resistance





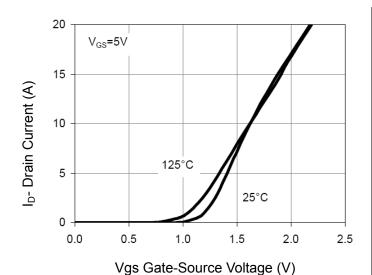
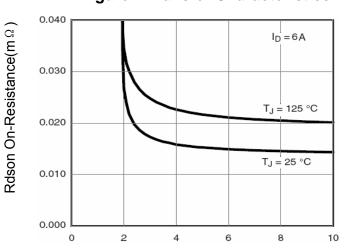


Figure 7 Transfer Characteristics



Vgs Gate-Source Voltage (V) Figure 9 Rdson vs Vgs

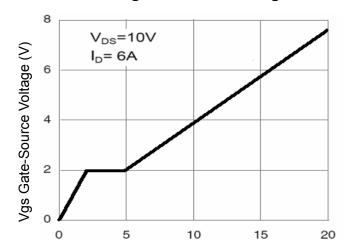


Figure 11 Gate Charge

Qg Gate Charge (nC)

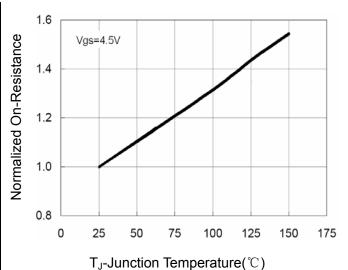
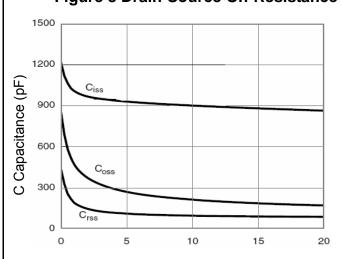
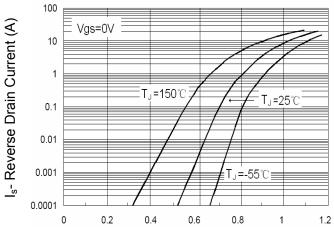


Figure 8 Drain-Source On-Resistance



Vds Drain-Source Voltage (V) Figure 10 Capacitance vs Vds



Vsd Source-Drain Voltage (V)

Figure 12 Source- Drain Diode Forward



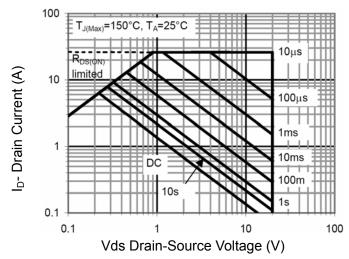


Figure 13 Safe Operation Area

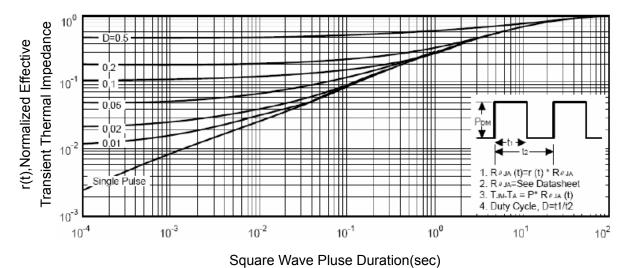
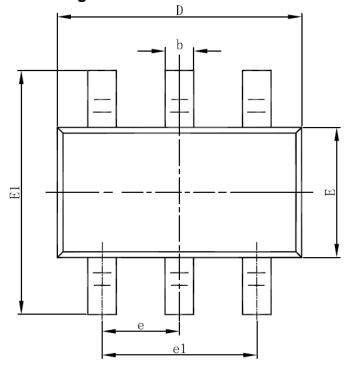


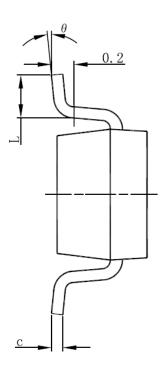
Figure 14 Normalized Maximum Transient Thermal Impedance

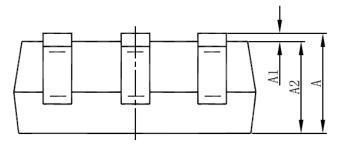


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SOT23-6L Package Information







Cl	Dimensions Ir	n Millimeters	Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	1.050	1.250	0.041	0.049	
A1	0.000	0.100	0.000	0.004	
A2	1.050	1.150	0.041	0.045	
b	0.300	0.500	0.012	0.020	
С	0.100	0.200	0.004	0.008	
D	2.820	3.020	0.111	0.119	
E	1.500	1.700	0.059	0.067	
E1	2.650	2.950	0.104	0.116	
е	0.950	(BSC)	0.037(BSC)		
e1	1.800	2.000	0.071	0.079	
L	0.300	0.600	0.012	0.024	
θ	0°	8°	0°	8°	



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